

SANYO Semiconductors DATA SHEET

SPA13003 (13003 series)

NPN Triple Diffused Planar Silicon Transistor

Switching Regulator Applications

Features

- · High breakdown voltage.
- · High-speed switching.
- · Wide ASO.
- · Adoption of MBIT process.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		700	V
Collector-to-Emitter Voltage	VCES		700	V
Collector-to-Emitter Voltage	VCEO		400	V
Emitter-to-Base Voltage	VEBO		8	V
Collector Current	IC		1	Α
Collector Current (Pulse)	ICP	PW≤300μs, duty cycle≤10%	2	Α
Base Current	IB		0.5	Α
Collector Dissipation	PC		0.6	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =400V, I _E =0A			10	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0A			10	μΑ
	hFE1	V _{CE} =5V, I _C =0.1A	15		35	
DC Current Gain	hFE2	V _{CE} =5V, I _C =0.5A	5			
	hFE3	V _{CE} =5V, I _C =1mA	7			

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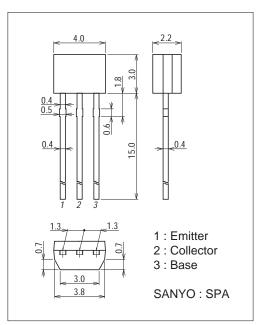
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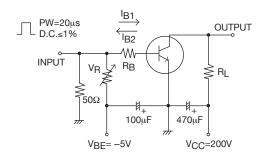
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =0.1A		20		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		10		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=0.5A, IB=0.1A			0.8	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =0.5A, I _B =0.1A			0.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =1mA, I _E =0A	700			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I _C =100μA, R _{BE} =0Ω	700			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=5mA, RBE=∞	400			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =1mA, I _C =0A	8			V
Turn-On Time	ton	I _C =0.5A, I _B 1=0.05A, I _B 2=-0.5A, R _L =400Ω, V _{CC} =200V			1.0	μS
Storage Time	t _{stg}	I _C =0.5A, I _B 1=0.05A, I _B 2=-0.5A, R _L =400Ω, V _{CC} =200V			1.0	μS
Fall Time	tf	I _C =0.5A, I _B 1=0.05A, I _B 2=-0.5A, R _L =400Ω, V _C C=200V			0.3	μs

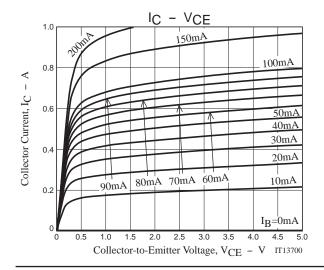
Package Dimensions

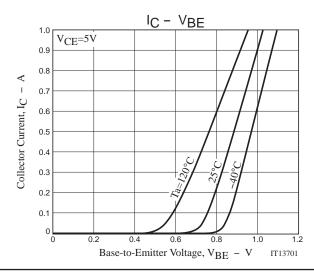
unit : mm (typ) 7524-004

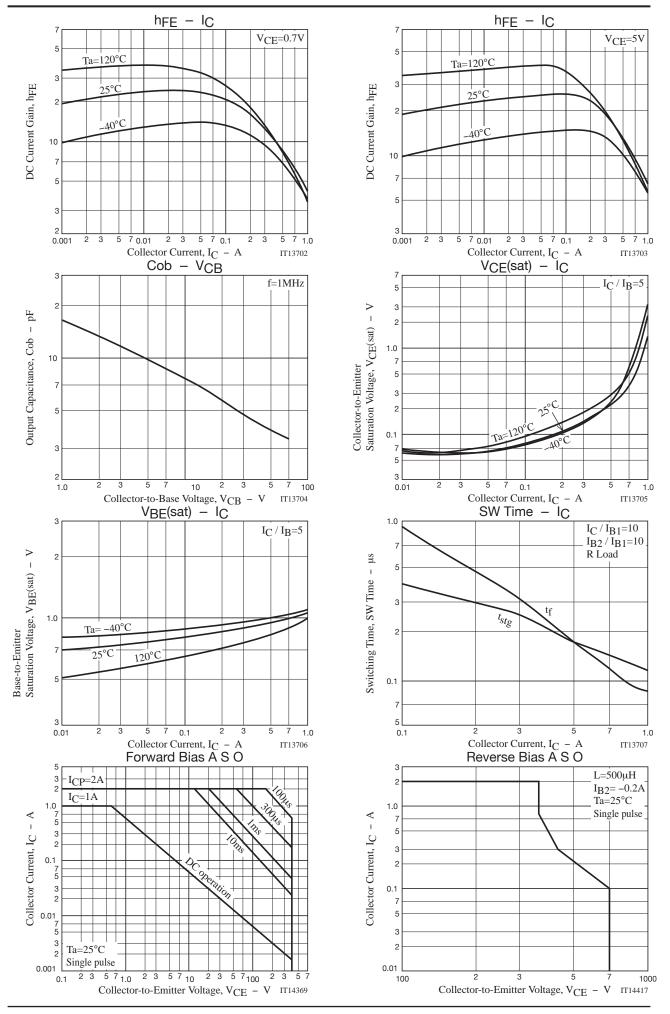


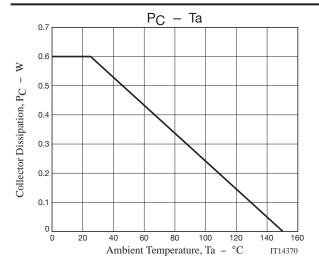
Switching Time Test Circuit











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